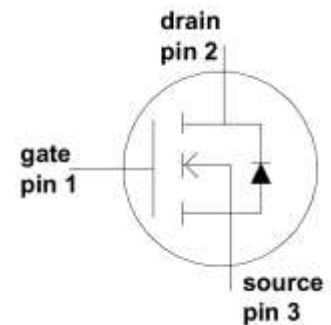


## Feature

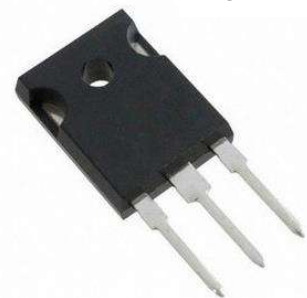
- 600V,80A  
 $R_{DS(ON)} < 30m\ \Omega @ V_{GS}=10V$
- Ultra-fast body diode
- Good Reliability
- 100% UIS and Isolation tested
- RoHs compliant



## Application

- Switch Mode Power Supply (SMPS )
- Uninterruptible Power Supply (UPS )
- Power Factor Correction (PFC)

TO-247-3L



## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
60R030	APC60R030WMF	TO-247-3L	-	-	600 per box

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Continuous Drain Current ( $T_a = 25^{\circ}C$ ) <sup>(1)</sup>	$I_D$	80	A
Continuous Drain Current ( $T_a = 100^{\circ}C$ ) <sup>(1)</sup>	$I_D$	50	A
Pulsed Drain Current <sup>(1)(2)</sup>	$I_{DM}$	240	A
Single Pulsed Avalanche Energy <sup>(3)</sup>	$E_{AS}$	3920	mJ
Power Dissipation	$P_D$	417	W
MOSFET dv/dt ruggedness	dV/dT	40	V/ns
Reverse diode dv/dt	dV/dT	40	V/ns
Thermal Resistance from Junction to Ambient, Steady-State <sup>(4)</sup>	$R_{\theta JA}$	32	$^{\circ}C/W$
Thermal Resistance from Junction to Case, Steady-State <sup>(4)</sup>	$R_{\theta JC}$	0.3	$^{\circ}C/W$
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55~ +150	$^{\circ}C$

**MOSFET ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

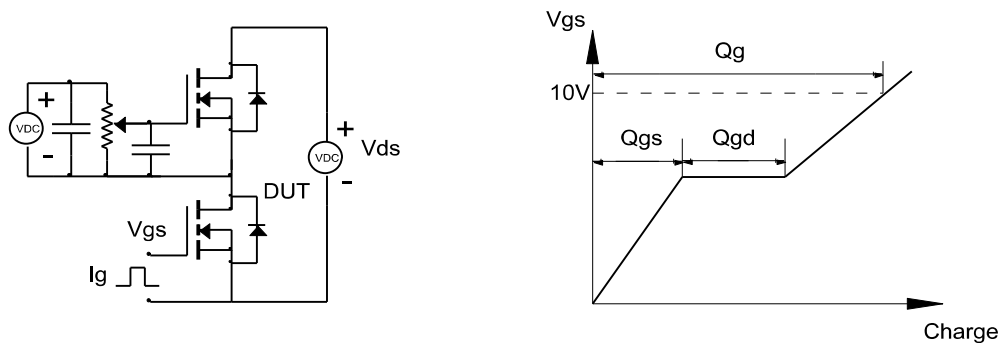
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	600	-	-	V
		V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA T <sub>J</sub> =125°C	-	650	-	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 600V, V <sub>GS</sub> = 0V, T <sub>J</sub> =25°C	-	-	1	uA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V	-	-	±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 2mA	2.5	3.3	4.5	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	-	25	30	mΩ
Gate Resistance	R <sub>G</sub>	f=1.0MHZ open drain	-	6.8	-	Ω
<b>Dynamic characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 100KHz	-	7699	-	pF
Output Capacitance	C <sub>oss</sub>		-	3091	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	2.1	-	
<b>Switching characteristics</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =480V, I <sub>D</sub> =40A, R <sub>G</sub> =25Ω, V <sub>GS</sub> =10V	-	56	-	ns
Turn-on rise time	t <sub>r</sub>		-	18.5	-	
Turn-off delay time	t <sub>d(off)</sub>		-	973	-	
Turn-off fall time	t <sub>f</sub>		-	62.5	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =480V, I <sub>D</sub> =40A, V <sub>GS</sub> =10V	-	272	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	32.6	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	159	-	
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 80A	-	0.87	-	V
Maximum Continuous Body-Diode Forward Current	I <sub>S</sub>				80	A
Maximum Pulsed Body-Diode Forward Current <sup>(1)</sup>	I <sub>SM</sub>				240	A
Peak Reverse Recovery Current	I <sub>rrm</sub>	V <sub>R</sub> =400V, I <sub>F</sub> =40A, di <sub>F</sub> /dt=100A/us	-	16	-	A
Reverse Recovery Time	Q <sub>rr</sub>		-	1.487	-	uC
Reverse Recovery Charge	T <sub>rr</sub>		-	170	-	ns

**Notes:**

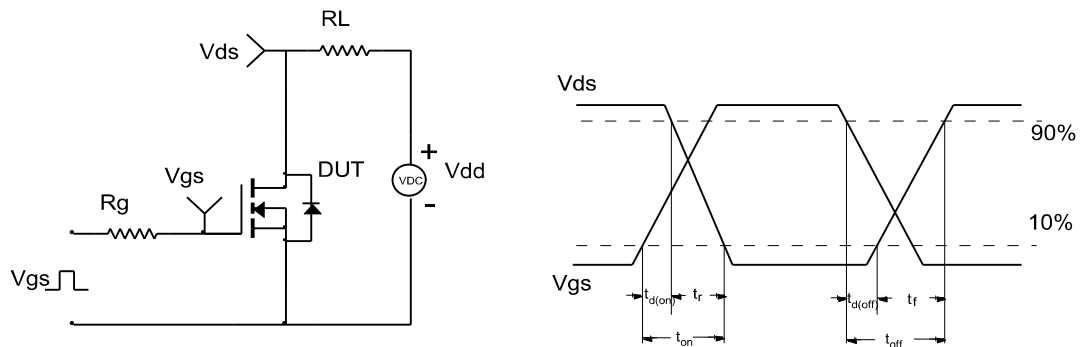
1. The max drain current rating limited by package and maximum junction temperature
2. Repetitive Rating:Pulse width limited by maximum junction temperature
3. EAS Condition:T<sub>J</sub>=25°C, V<sub>DD</sub>=150V, R<sub>G</sub>=25 Ω, L=10mH, I<sub>AS</sub>=28A
4. Mount on minimum PCB layout

## Test Circuit and Waveform

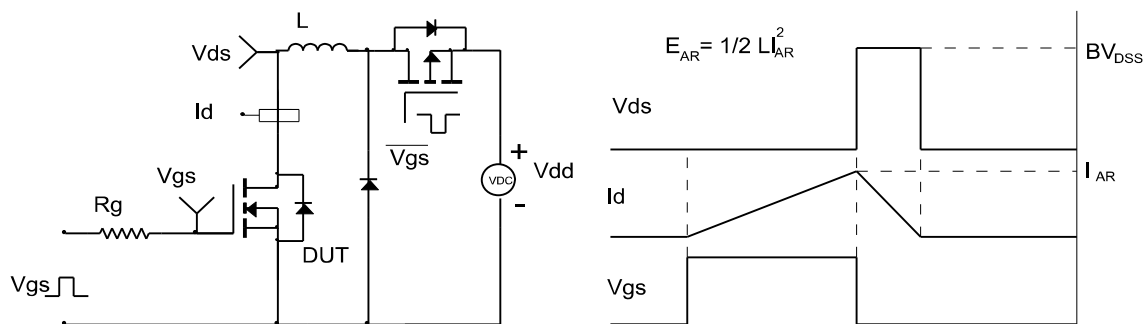
Gate Charge Test Circuit & Waveform



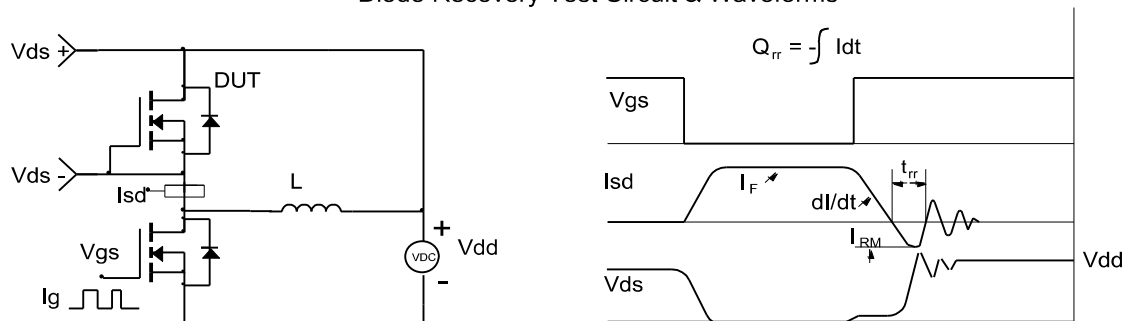
Resistive Switching Test Circuit & Waveforms



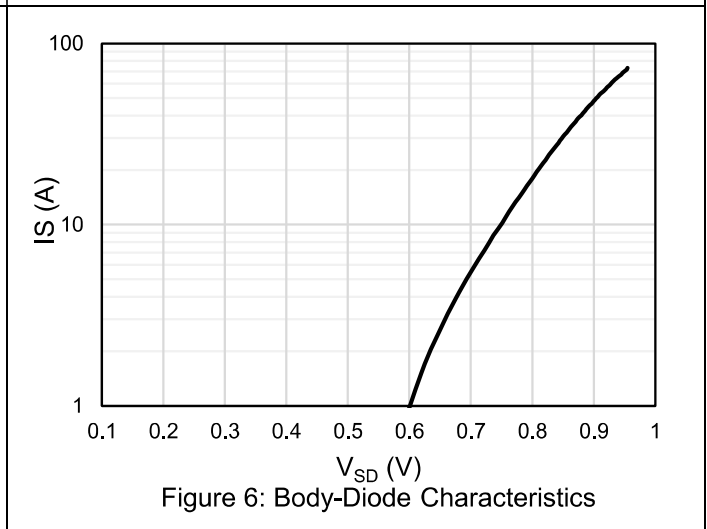
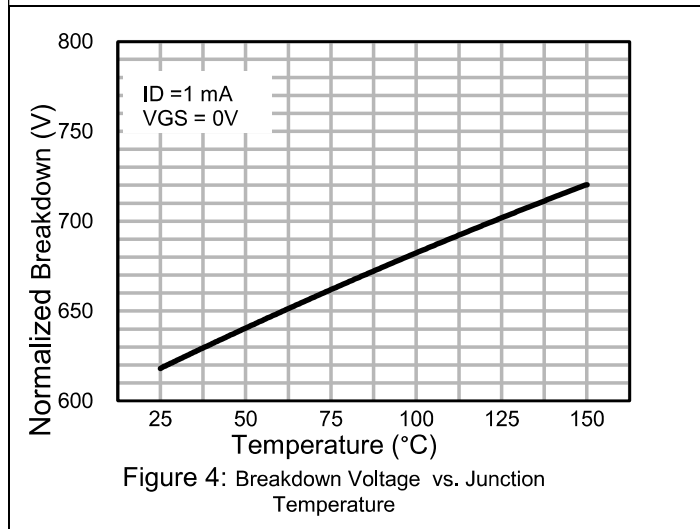
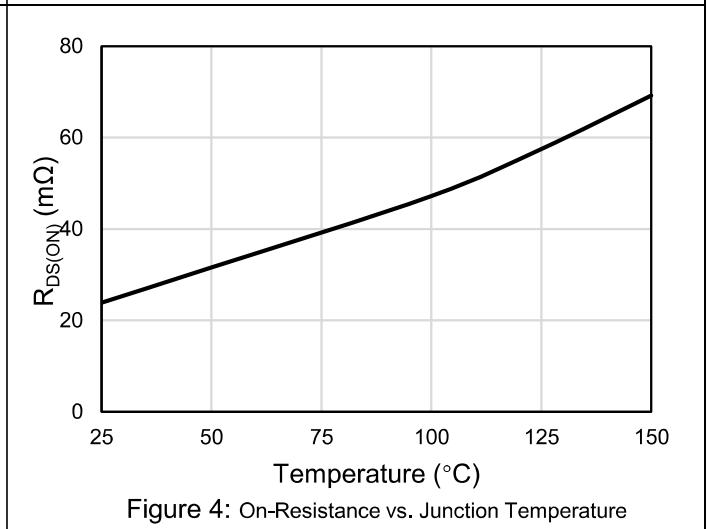
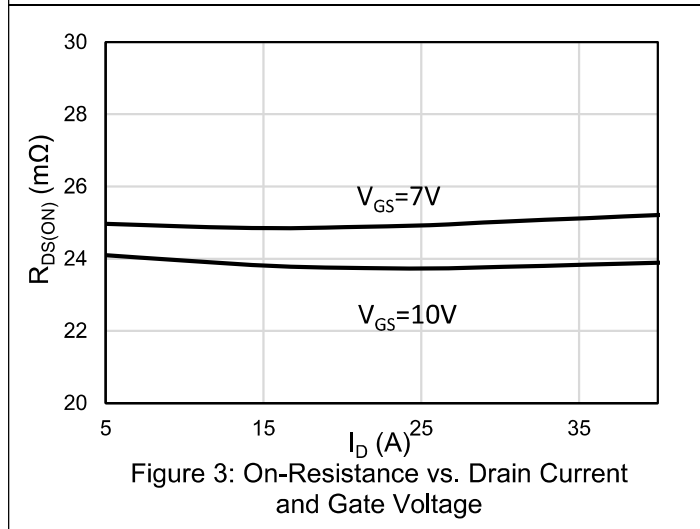
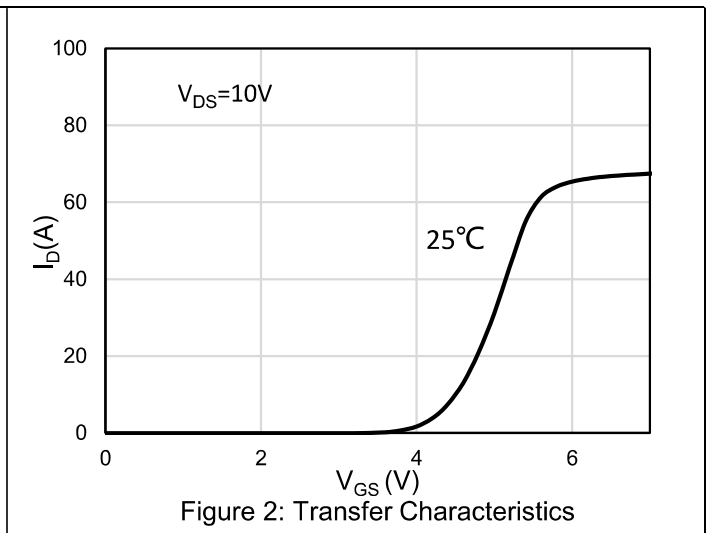
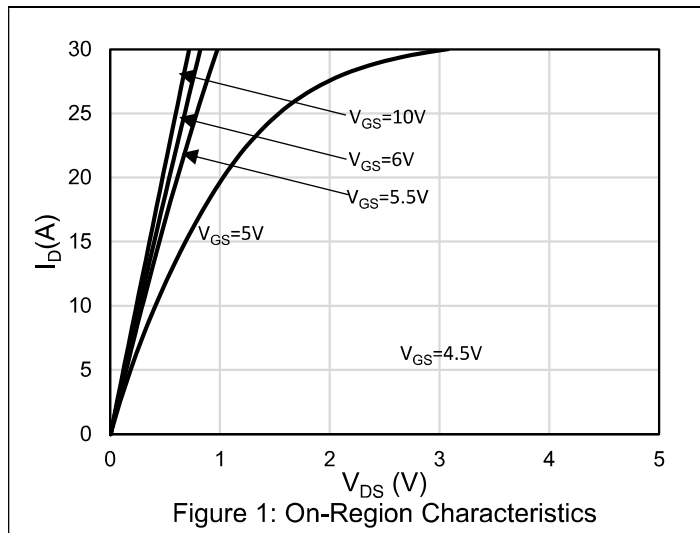
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

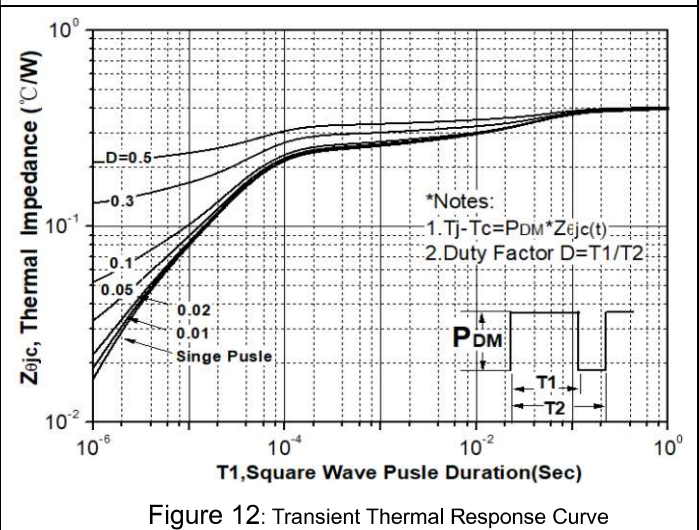
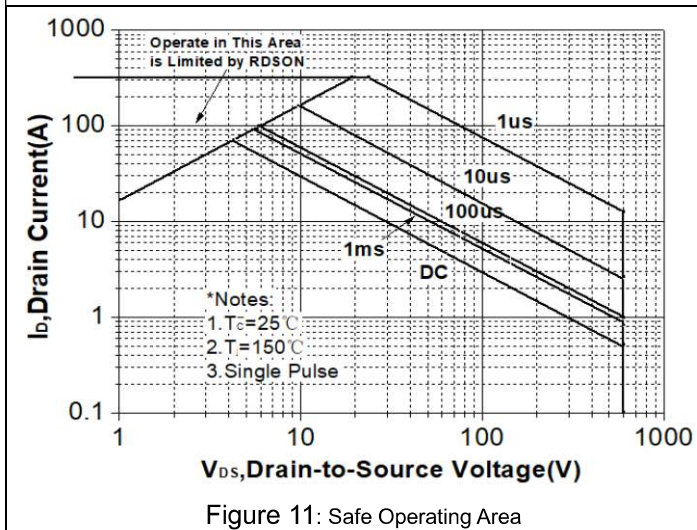
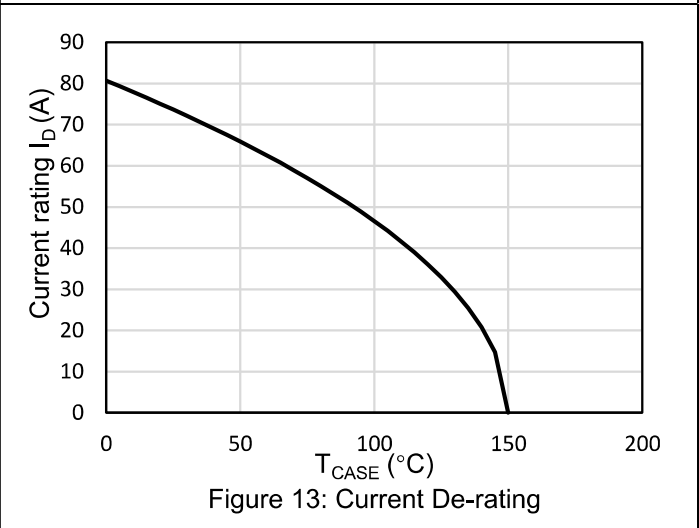
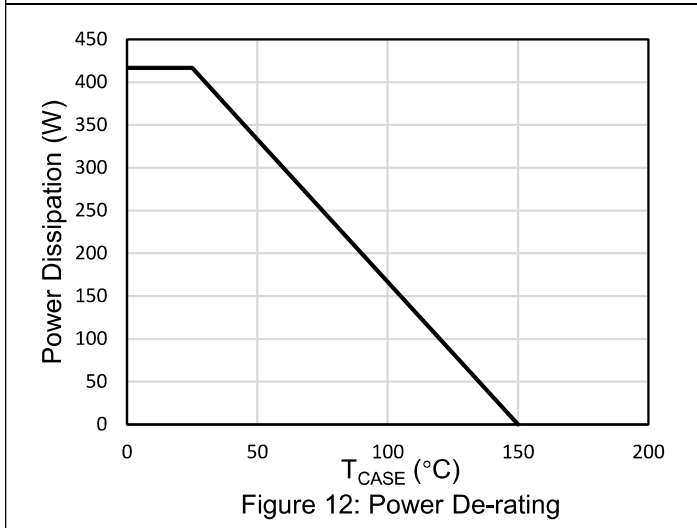
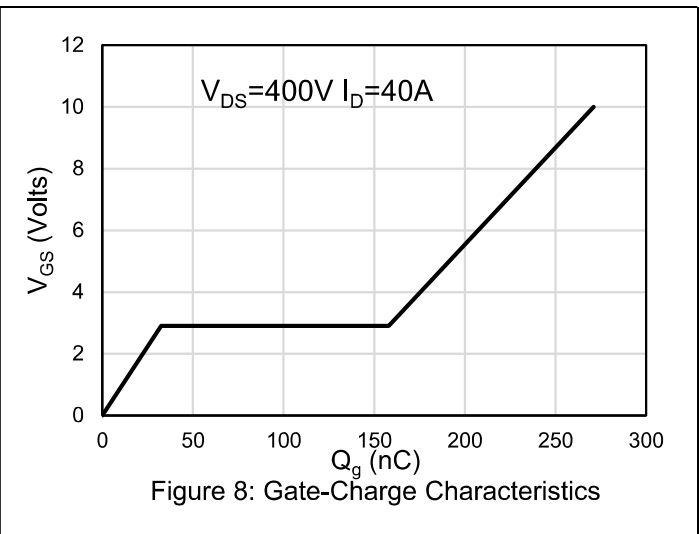
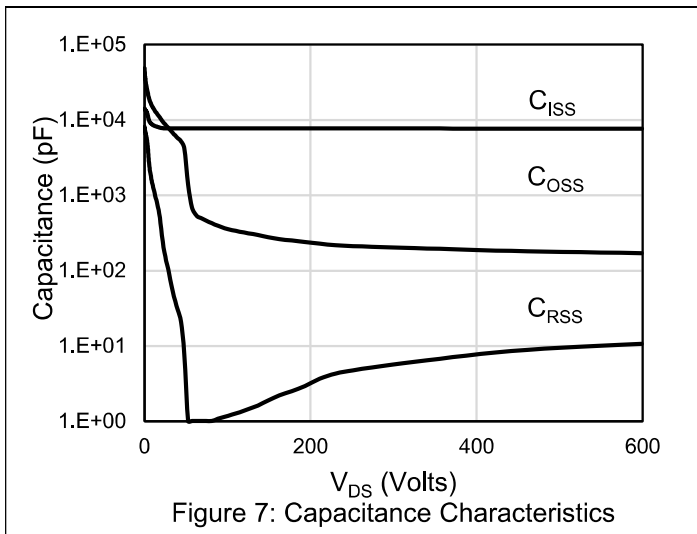


Diode Recovery Test Circuit & Waveforms

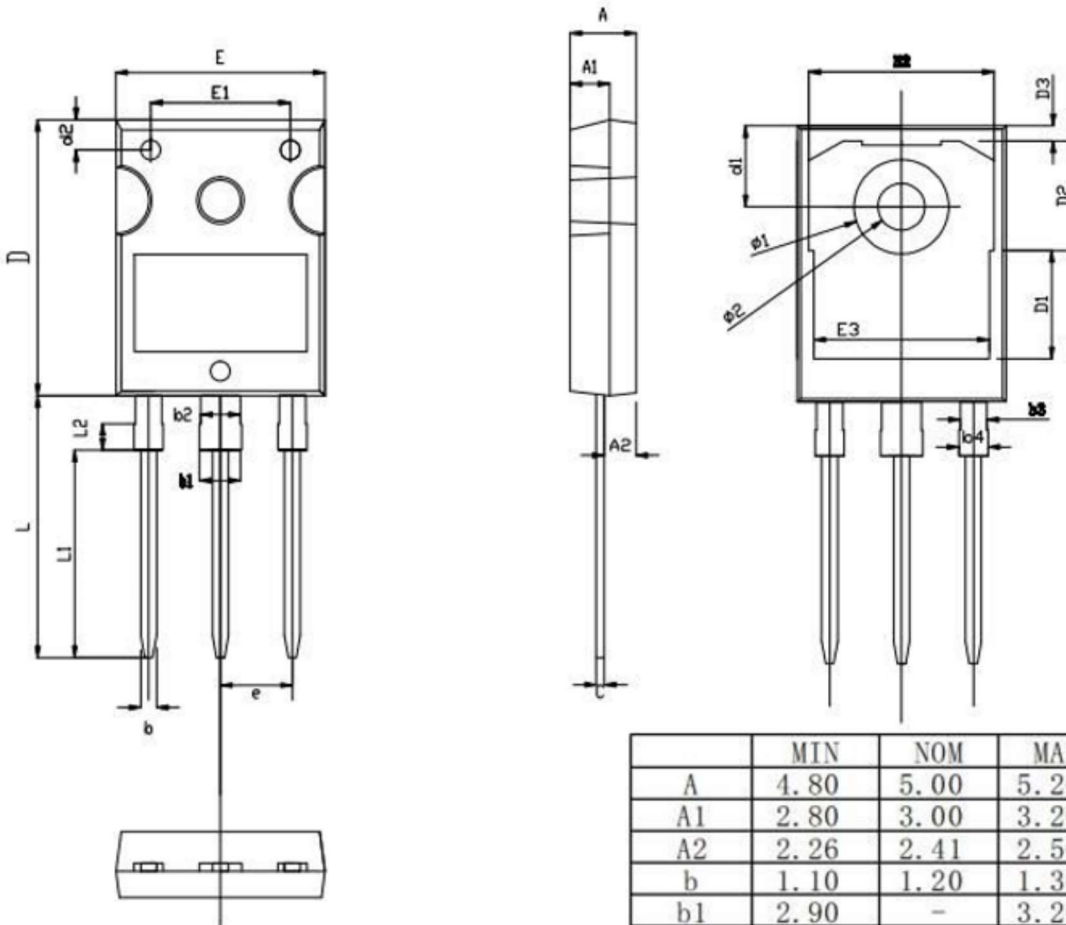


**Electrical Characteristics Diagrams**

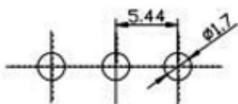




TO-247-3L PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



UNIT: mm

	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.80	3.00	3.20
A2	2.26	2.41	2.56
b	1.10	1.20	1.30
b1	2.90	-	3.20
b2	2.90	3.00	3.10
b3	1.90	2.00	2.10
b4	2.00	-	2.20
c	0.50	0.60	0.70
D	20.80	21.00	21.20
D1		8.23	
D2		8.32	
D3		1.17	
d1	6.00	6.15	6.30
d2	2.20	2.30	2.40
E	15.60	15.80	16.00
E1		10.50	
E2		14.02	
E3		13.50	
e	5.34	5.44	5.54
L	19.72	19.92	20.12
L1		15.79	
L2		1.98	
Ø1	7.10	7.19	7.30
Ø2	3.50	3.60	3.70